

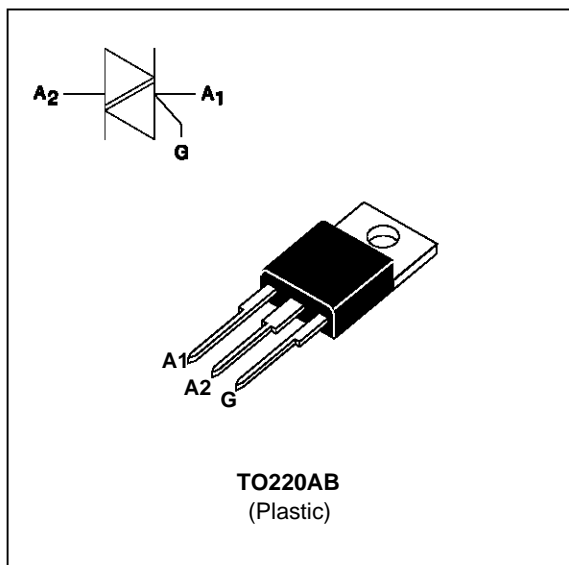
**STANDARD TRIACS**

**FEATURES**

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION :  $(dV/dt)_c > 5 \text{ V}/\mu\text{s}$
- BTA Family :  
INSULATING VOLTAGE= 2500V(RMS)  
(UL RECOGNIZED : E81734)

**DESCRIPTION**

The BTA/BTB06 B/C triac family are high performance glass passivated PNP devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



**ABSOLUTE RATINGS** (limiting values)

| Symbol                             | Parameter  |     | Value                   | Unit                           |                  |
|------------------------------------|--|-----|-------------------------|--------------------------------|------------------|
| I <sub>T(RMS)</sub>                | RMS on-state current<br>(360° conduction angle)  | BTA | T <sub>c</sub> = 100 °C | 6                              | A                |
|                                    |  | BTB | T <sub>c</sub> = 105 °C |                                |                  |
| I <sub>TSM</sub>                   | Non repetitive surge peak on-state current<br>( T <sub>j</sub> initial = 25°C )                                  |     | t <sub>p</sub> = 8.3 ms | 63                             | A                |
|                                    |  |     | t <sub>p</sub> = 10 ms  | 60                             |                  |
| I <sup>2</sup> t                   | I <sup>2</sup> t value   |     | t <sub>p</sub> = 10 ms  | 18                             | A <sup>2</sup> s |
| dI/dt                              | Critical rate of rise of on-state current<br>Gate supply : I <sub>G</sub> = 500mA    di <sub>G</sub> /dt = 1A/μs |     | Repetitive<br>F = 50 Hz | 10                             | A/μs             |
|                                    |  |     | Non Repetitive          | 50                             |                  |
| T <sub>stg</sub><br>T <sub>j</sub> | Storage and operating junction temperature range   |     |                         | - 40 to + 150<br>- 40 to + 125 | °C<br>°C         |
| T <sub>l</sub>                     | Maximum lead temperature for soldering during 10 s at 4.5 mm from case   |     |                         | 260                            | °C               |

| Symbol                               | Parameter  | BTA / BTB06... B/C |     |     |     | Unit |
|--------------------------------------|--|--------------------|-----|-----|-----|------|
|                                      |  | 400                | 600 | 700 | 800 |      |
| V <sub>DRM</sub><br>V <sub>RRM</sub> | Repetitive peak off-state voltage<br>T <sub>j</sub> = 125 °C | 400                | 600 | 700 | 800 | V    |

**THERMAL RESISTANCES**

| Symbol       | Parameter   |     | Value | Unit |
|--------------|---|-----|-------|------|
| Rth (j-a)    | Junction to ambient                                       |     | 60    | °C/W |
| Rth (j-c) DC | Junction to case for DC                                   | BTA | 4.4   | °C/W |
|              |   | BTB | 3.2   |      |
| Rth (j-c) AC | Junction to case for 360° conduction angle<br>( F= 50 Hz) | BTA | 3.3   | °C/W |
|              |   | BTB | 2.4   |      |

**GATE CHARACTERISTICS (maximum values)**

PG (AV) = 1W    PGM = 10W (tp = 20 μs)    IGM = 4A (tp = 20 μs)    VGM = 16V (tp = 20 μs).

**ELECTRICAL CHARACTERISTICS**

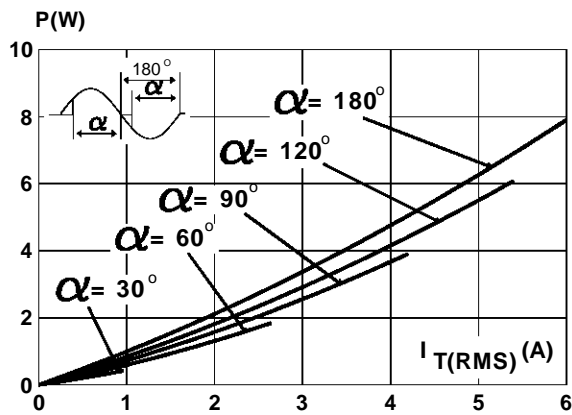
| Symbol       | Test Conditions                            | Quadrant |             | Suffix |      | Unit |      |
|--------------|--|----------|-------------|--------|------|------|------|
|              |  |          |             | B      | C    |      |      |
| IGT          | VD=12V (DC) RL=33Ω                         | Tj=25°C  | I-II-III    | MAX    | 50   | 25   | mA   |
|              |  |          | IV          | MAX    | 100  | 50   |      |
| VGT          | VD=12V (DC) RL=33Ω                         | Tj=25°C  | I-II-III-IV | MAX    | 1.5  |      | V    |
| VGD          | VD=VDRM RL=3.3kΩ                           | Tj=110°C | I-II-III-IV | MIN    | 0.2  |      | V    |
| tgt          | VD=VDRM IG = 500mA<br>dIG/dt = 3A/μs       | Tj=25°C  | I-II-III-IV | TYP    | 2    |      | μs   |
| IL           | IG=1.2 IGT                                 | Tj=25°C  | I-III-IV    | TYP    | 40   | 20   | mA   |
|              |  |          | II          |        | 70   | 35   |      |
| IH *         | IT= 500mA gate open                        | Tj=25°C  |             | MAX    | 50   | 25   | mA   |
| VTM *        | ITM= 8.5A tp= 380μs                        | Tj=25°C  |             | MAX    | 1.65 |      | V    |
| IDRM<br>IRRM | VDRM Rated<br>VRRM Rated                   | Tj=25°C  |             | MAX    | 0.01 |      | mA   |
|              |  | Tj=110°C |             | MAX    | 0.5  |      |      |
| dV/dt *      | Linear slope up to VD=67%VDRM<br>gate open | Tj=110°C |             | MIN    | 250  | 100  | V/μs |
| (dV/dt)c *   | (dI/dt)c = 2.7A/ms                         | Tj=110°C |             | MIN    | 10   | 5    | V/μs |

\* For either polarity of electrode A2 voltage with reference to electrode A1.

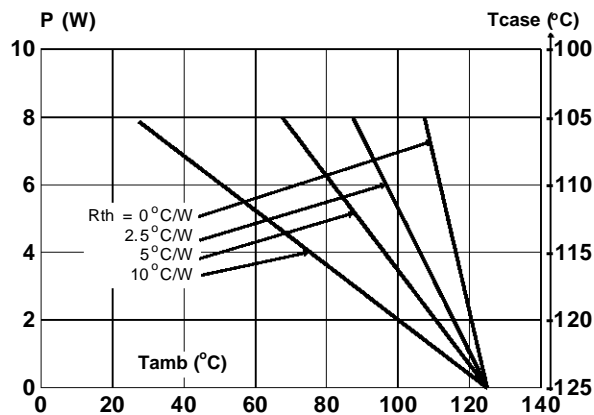
ORDERING INFORMATION

| Package              | $I_T(RMS)$ | $V_{DRM} / V_{RRM}$ | Sensitivity Specification |   |
|----------------------|------------|---------------------|---------------------------|---|
|                      | A          | V                   | B                         | C |
| BTA<br>(Insulated)   | 6          | 400                 | X                         | X |
|                      |            | 600                 | X                         | X |
|                      |            | 700                 | X                         | X |
|                      |            | 800                 | X                         | X |
| BTB<br>(Uninsulated) | 6          | 400                 | X                         | X |
|                      |            | 600                 | X                         | X |
|                      |            | 700                 | X                         | X |
|                      |            | 800                 | X                         | X |

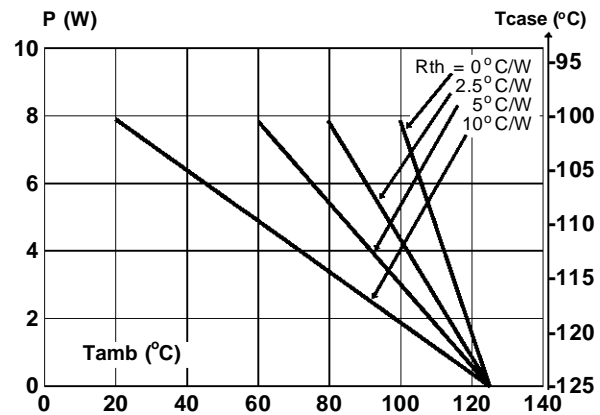
**Fig.1** : Maximum RMS power dissipation versus RMS on-state current ( $F=50Hz$ ).  
(Curves are cut off by  $(di/dt)_c$  limitation)



**Fig.3** : Correlation between maximum mean power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact (BTB).



**Fig.2** : Correlation between maximum RMS power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact (BTA).



**Fig.4** : RMS on-state current versus case temperature.

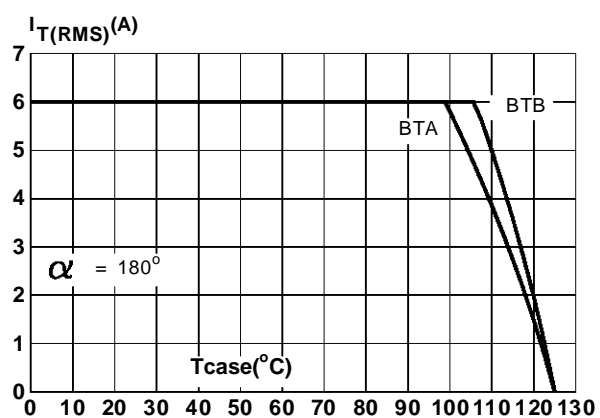


Fig.5 : Relative variation of thermal impedance versus pulse duration.

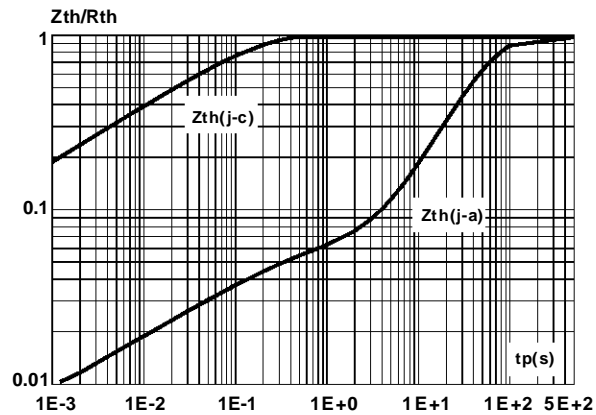


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

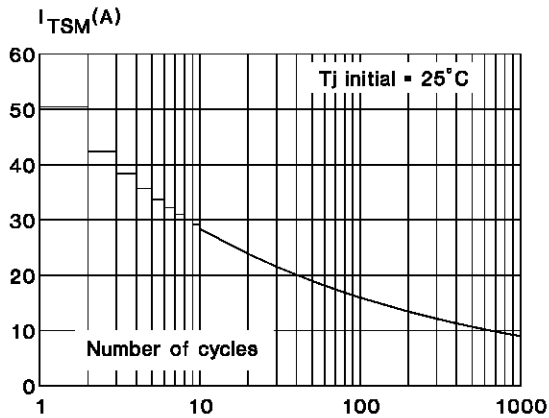


Fig.9 : On-state characteristics (maximum values).

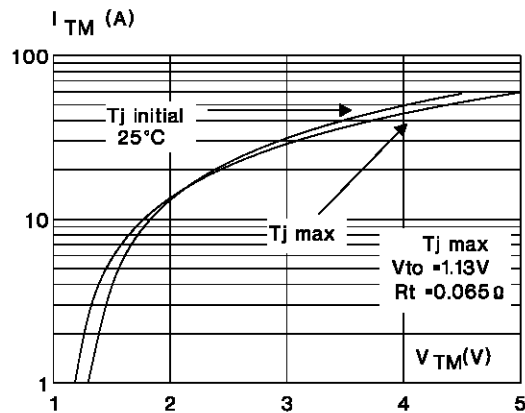


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

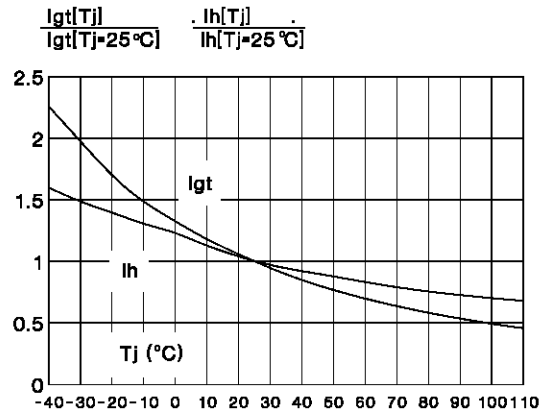
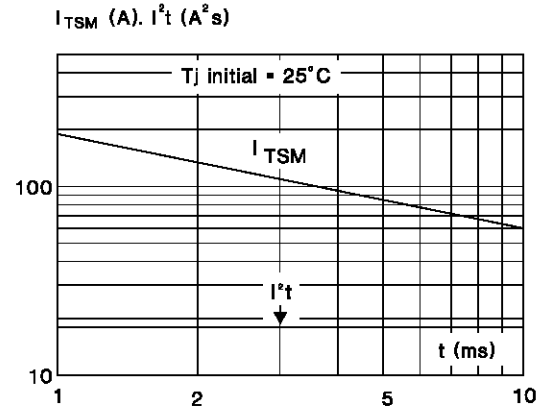
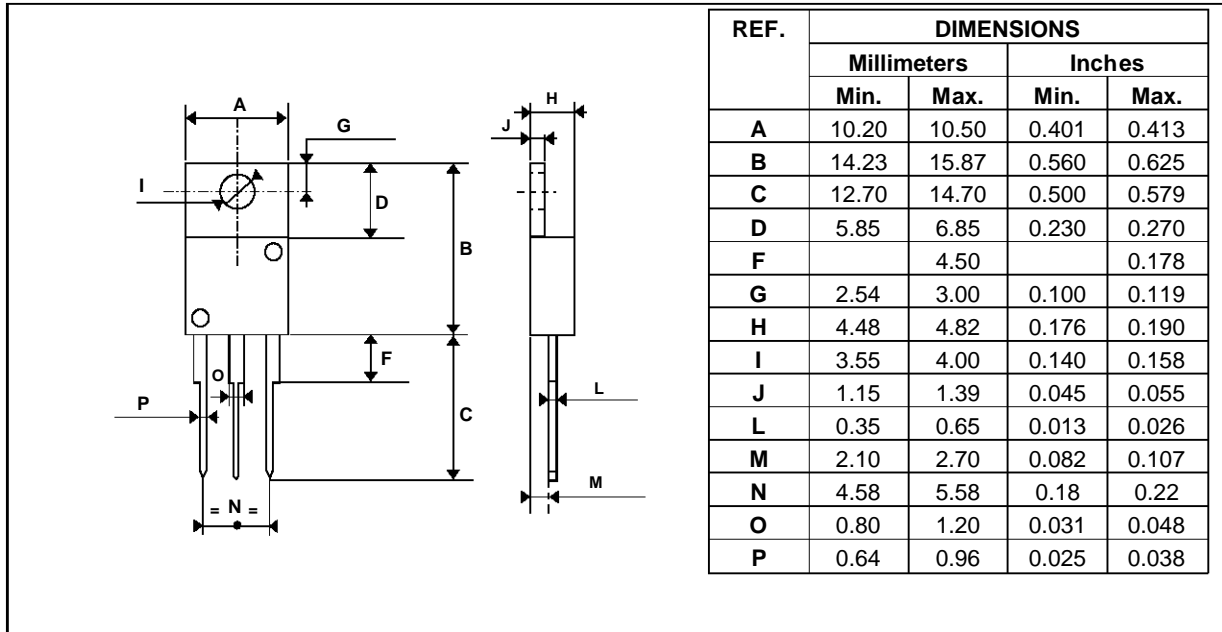


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \leq 10ms$ , and corresponding value of  $I^2t$ .



**PACKAGE MECHANICAL DATA**

TO220AB Plastic



Cooling method : C  
 Marking : type number  
 Weight : 2.3 g  
 Recommended torque value : 0.8 m.N.  
 Maximum torque value : 1 m.N.

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